

Please add new claims 32 and 33 as follows:

--32. A method of forming a film on a substrate comprising the steps of:

placing a substrate in a reaction chamber;
introducing a reactive gas comprising at least TEOS;
exciting said reactive gas by supplying photo and electrical energies into said reaction chamber; and
depositing a film on said substrate by CVD wherein said TEOS is in a liquid state during deposition.

33. A method of forming a film on a substrate comprising the steps of:
placing a substrate in a reaction chamber;
introducing a reactive gas comprising at least TEOS;
supplying photo energies and plasma energies simultaneously in order to decompose said reactive gas;
depositing a film on said substrate, wherein said TEOS is in a liquid state during deposition.--

REMARKS

The Examiner's action of April 22, 1994 was received and carefully reviewed. Initially, Applicants acknowledge with appreciation the Examiner's interview of July 21, 1994. The claims of the instant application are amended to place this case in a condition for allowance. Claims 17, 19-22, 24-30, 32 and 33 are currently pending in the instant application.

Specifically, rejected claims 16, 18 and 23 are cancelled. Further, claims 19-21, 25, 29 and 30 are amended to depend from allowed claims 17, 22 and 24. Claim 31 is also cancelled in view of Applicants' election. Of